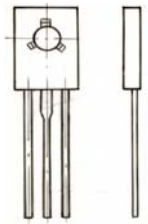
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-126 Plastic-Encapsulate Transistors

BD034 TRANSISTOR (PNP)

TO-126



1. EMITTER
2. COLLECTOR
3. BASE

1 2 3

FEATURES

Power dissipation

$P_{CM:}$ 1.25 W (Tamb=25℃)

Collector current

$I_{CM:}$ -2.5 A

Collector-base voltage

$V_{(BR)CBO}$: -110 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA, I_E=0	-110			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-10mA, I_B=0	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-100V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-100mA	100		560	
	$h_{FE(2)}$	V_{CE}=-2V, I_C=-1.5A	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A, I_B=-200mA			-0.5	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA			-1	V
Transition frequency	f_T	V_{CE}=-1V, I_C=-250mA, f=1MHz	3			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560

TypicalCharacteristics BD034

